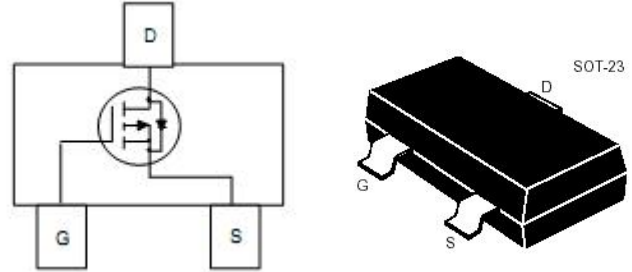




GM2311

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



P-Channel Enhancement-Mode MOS FETs

P 溝道增強型 MOS 場效應管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	-60	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 20	V
Drain Current (continuous) 漏極電流-連續	I_D	-1.8	A
Drain Current (pulsed) 漏極電流-脈沖	I_{DM}	-6	A
Total Device Dissipation 總耗散功率 $T_A=25^\circ\text{C}$ 環境溫度為 25°C	P_D	1000	mW
Junction 結溫	T_J	150	$^\circ\text{C}$
Storage Temperature 儲存溫度	T_{stg}	-55to+150	$^\circ\text{C}$

■DEVICE MARKING 打標

GM2311=E11

GM2311

■ ELECTRICAL CHARACTERISTICS 電特性
(T_A=25°C unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I _D = -250uA, V _{GS} =0V)	BV _{DSS}	-60	—	—	V
Gate Threshold Voltage 柵極開啓電壓(I _D = -250uA, V _{GS} = V _{DS})	V _{GS(th)}	-1	—	-3	V
Diode Forward Voltage Drop 內附二極管正向壓降(I _S = -1.2A, V _{GS} =0V)	V _{SD}	—	—	-1.2	V
Zero Gate Voltage Drain Current 零柵壓漏極電流(V _{GS} =0V, V _{DS} = -60V)	I _{DSS}	—	—	-10	uA
Gate Body Leakage 柵極漏電流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 靜態漏源導通電阻(I _D = -1.8A, V _{GS} = -10V)	R _{DS(ON)}	—	200	250	mΩ
Static Drain-Source On-State Resistance 靜態漏源導通電阻(I _D = -1.4A, V _{GS} = -4.5V)	R _{DS(ON)}	—	240	300	mΩ
Input Capacitance 輸入電容 (V _{GS} =0V, V _{DS} = -25V, f=1MHz)	C _{ISS}	—	364	—	pF
Output Capacitance 輸出電容 (V _{GS} =0V, V _{DS} = -25V, f=1MHz)	C _{OSS}	—	41	—	pF
Turn-ON Time 開啓時間 (V _{DS} = -30V, I _D = -1A, R _{GEN} =3.3Ω)	t _(on)	—	20	—	ns
Turn-OFF Time 關斷時間 (V _{DS} = -30V, I _D = -1A, R _{GEN} =3.3Ω)	t _(off)	—	5.2	—	ns

Pulse Width≤300 μs; Duty Cycle≤2.0%